

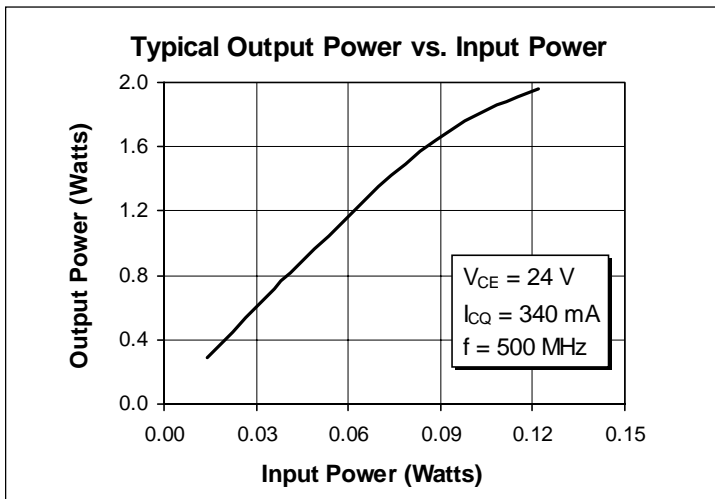
PTB 20204

1.0 Watt, 380–500 MHz RF Power Transistor

Description

The 20204 is a class A, NPN, common emitter RF power transistor intended for 24 Vdc operation from 380 to 500 MHz. Rated at 1.0 watt minimum output power, it may be used for both CW and PEP applications. Ion implantation, nitride surface passivation and gold metallization ensure excellent device reliability. 100% lot traceability is standard.

- 1.0 Watt, 380–500 MHz
- Class A Characteristics
- -40 dB Max Two-Tone IMD at 1.0 W(PEP)
- Gold Metallization
- Silicon Nitride Passivated



Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|-----------------|--------------|------------------------------|
| Collector-Emitter Voltage | V_{CE} | 60 | Vdc |
| Collector-Base Voltage | V_{CBO} | 60 | Vdc |
| Emitter-Base Voltage (collector open) | V_{EBO} | 4.0 | Vdc |
| Collector Current (continuous) | I_C | 0.5 | Adc |
| Total Device Dissipation at $T_{flange} = 25^\circ\text{C}$ Above 25°C derate by | P_D | 11 0.0625 | Watts W/ $^\circ\text{C}$ |
| Storage Temperature Range | T_{STG} | -40 to +150 | $^\circ\text{C}$ |
| Thermal Resistance ($T_{flange} = 70^\circ\text{C}$) | $R_{\theta JC}$ | 16 | $^\circ\text{C}/\text{W}$ |

Electrical Characteristics (100% Tested)

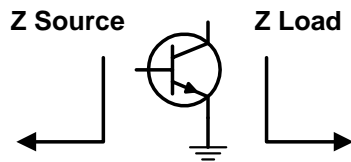
| Characteristic | Conditions | Symbol | Min | Typ | Max | Units |
|--------------------------|--|---------------|-----|-----|-----|-------|
| Breakdown Voltage C to E | $I_B = 0\text{ A}, I_C = 5\text{ mA}$ | $V_{(BR)CEO}$ | 25 | 30 | — | Volts |
| Breakdown Voltage C to E | $V_{BE} = 0\text{ V}, I_C = 5\text{ mA}$ | $V_{(BR)CES}$ | 70 | — | — | Volts |
| Breakdown Voltage E to B | $I_C = 0\text{ A}, I_E = 5\text{ mA}$ | $V_{(BR)EBO}$ | 4 | 5 | — | Volts |
| DC Current Gain | $V_{CE} = 5\text{ V}, I_C = 250\text{ mA}$ | h_{FE} | 20 | 40 | — | — |
| Output Capacitance | $V_{CB} = 24\text{ V}, I_E = 0\text{ A}, f = 1\text{ MHz}$ | C_{obo} | — | 4.4 | — | pF |

RF Specifications (100% Tested)

| Characteristic | Symbol | Min | Typ | Max | Units |
|---|----------|------|------|------|-------|
| Gain ($V_{CE} = 24\text{ Vdc}, P_{out} = 1.0\text{ W}, I_{CQ} = 340\text{ mA}, f = 500\text{ MHz}$) | G_{pe} | 12.5 | 13.5 | — | dB |
| Two-Tone Intermodulation Distortion ($V_{CE} = 24\text{ Vdc}, P_{out} = 1.0\text{ W(PEP)}, I_{CQ} = 340\text{ mA}, f_1 = 500\text{ MHz}, f_2 = 501\text{ MHz}$) | IM_2 | — | -44 | -40 | dB |
| Load Mismatch Tolerance ($V_{CE} = 24\text{ Vdc}, P_{out} = 2\text{ W}, I_{CQ} = 340\text{ mA}, f = 500\text{ MHz}$ —all phase angles at frequency of test) | Ψ | — | — | 30:1 | — |

Impedance Data (data shown for fixed-tuned broadband circuit)

($V_{CE} = 24\text{ Vdc}, P_{out} = 1.0\text{ W}, I_{CQ} = 340\text{ mA}$)



| Frequency MHz | Z Source | | Z Load | |
|------------------|----------|------|--------|------|
| | R | jX | R | jX |
| 400 | 6.0 | -4.0 | 33.2 | 24.9 |
| 450 | 3.9 | -0.6 | 34.0 | 17.3 |
| 500 | 3.4 | 2.1 | 30.1 | 12.2 |

